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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/765,477	01/28/2004	Leonard Forbes	M4065.0381/P381-A	9433
24998	7590	12/12/2006	EXAMINER	
DICKSTEIN SHAPIRO LLP 1825 EYE STREET NW Washington, DC 20006-5403			THOMAS, TONIAE M	
		ART UNIT	PAPER NUMBER	
		2822		

DATE MAILED: 12/12/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)
	10/765,477	FORBES ET AL.
	Examiner Toniae M. Thomas	Art Unit 2822

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 13 November 2006.

2a) This action is **FINAL**. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 68-91 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5) Claim(s) 89 is/are allowed.

6) Claim(s) 68,90 and 91 is/are rejected.

7) Claim(s) 69-88 is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on 28 January 2004 is/are: a) accepted or b) objected to by the Examiner.

 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a))

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/VMail Date

4) Interview Summary (PTO-413)
Paper No(s)/Mail Date. ____ .

5) Notice of Informal Patent Application (PTO-152)

6) Other: _____

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 13 November 2006 has been entered.
2. Currently, claims 68-91 are pending

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

3. Claims 68, 90, and 91 are rejected under 35 U.S.C. 102(e) as being anticipated by Yu (US 6,312,995 B1).

Regarding claim 68

Yu discloses a method of forming a semiconductor transistor (figs. 1, 2a-2e and accompanying text). The method comprises: forming a first gate

dielectric 112 over a substrate 110 (fig. 2a and col. 3, lines 58-62); forming a first type conductive gate region 114 over the first gate dielectric (fig. 2a and col. 3, line 62 - col. 4, line 3); forming a dielectric layer 117 on the sides of the first type conductive layer (fig. 2a and col. 4, lines 8-10); forming a second gate dielectric 117 over the substrate (fig. 112)¹; forming a second type conductive gate region 124 over the second gate dielectric, adjacent to the dielectric layer 117, and on the sides of the first type conductive region (fig. 2d and col. 4, lines 35-52); and forming source and drain regions 120 in the substrate to define a channel region between them and beneath the first and second conductive type gate regions (fig. 2d and col. 4, lines 19-22), wherein all portions of the first gate dielectric, first type conductive gate region, second gate dielectric, and second type conductive gate region are wholly between the source and drain regions.

Regarding claims 90 and 91

Again, Yu discloses a method of forming a semiconductor transistor (figs. 2a-2e and accompanying text). The method comprises: providing a substrate 110 (fig. 2a); forming a first gate dielectric layer 112 over the substrate (fig. 2a); forming a first gate electrode 114 having sidewalls over the first gate dielectric layer (fig. 2a), wherein the first gate electrode has a first work function (fig. 1 and col. 3, lines 7-11); forming a dielectric layer 117 on the sidewalls of the first gate electrode (fig. 2a); forming a second gate dielectric 112 over the

¹ The second gate dielectric layer is that portion of the dielectric layer 112 not covered by the

substrate (fig. 2c, see Footnote No. 1); forming a pair of second gate electrodes 124 over the second gate dielectric and adjacent to the dielectric layer 117, the second gate electrodes being separated from the first gate electrode by the dielectric layer (fig. 2d), wherein the pair of second gate electrodes has a second work function which is different than the first work function (fig. 1 and col. 3, lines 7-11); forming a conductive cap 128 over each of the gate electrodes (fig. 2e and col. 5, lines 1-4); forming insulating sidewalls 118 adjacent to the conductive cap and the gate electrodes (fig. 2e and col. 4, lines 18-22), and forming source and drain regions 120 in the substrate to define a channel region between them and beneath the first and second conductive type gate regions (fig. 2d), wherein all portions of the first gate dielectric, first type conductive gate region, second gate dielectric, and second type conductive gate region are wholly between the source and drain regions.

The second work function is more negative than the first work function (col. 3, lines 11-24).

Allowable Subject Matter

4. Claims 69-88 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Claim 89 is allowable over the prior art of record.

Response to Arguments

5. Applicant's arguments with respect to claims 68, 69, 90 and 91 have been considered but are moot in view of the new ground(s) of rejection.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Toniae M. Thomas whose telephone number is (571) 272-1846. The examiner can normally be reached on Monday through Friday from 8:30 a.m. to 5:30 p.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on (571) 272-2429. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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Toniae M. Thomas
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Art Unit 2822

TMT
07 August 2006